



No.4308

2SJ288

P-Channel MOS Silicon FET

Very High-Speed
Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

Absolute Maximum Ratings at Ta = 25°C

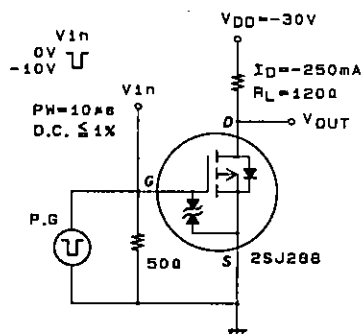
			unit
Drain to Source Voltage	V _{DSS}	-60	V
Gate to Source Voltage	V _{GS}	±15	V
Drain Current(DC)	I _D	-500	mA
Drain Current(Pulse)	I _{DP}	PW ≤ 10 μs, duty cycle ≤ 1%	A
Allowable Power Dissipation	P _D	T _c = 25°C	3.5 W
		Mounted on ceramic board (250mm ² × 0.8mm)	1.3 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60V, V _{GS} = 0			-100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -250mA	240	400		mS
Static Drain to Source on State Resistance	R _{DS(on)}	I _D = -250mA, V _{GS} = -10V		2.2	3.0	Ω
	R _{DS(on)}	I _D = -250mA, V _{GS} = -4V		3.0	4.0	Ω
Input Capacitance	C _{iss}	V _{DS} = -20V, f = 1MHz		45		pF
Output Capacitance	C _{oss}	V _{DS} = -20V, f = 1MHz		20		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -20V, f = 1MHz		5		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		7		ns
Rise Time	t _r	"		10		ns
Turn-OFF Delay Time	t _{d(off)}	"		35		ns
Fall Time	t _f	"		20		ns
Diode Forward Voltage	V _{SD}	I _S = -500mA, V _{GS} = 0		-1		V

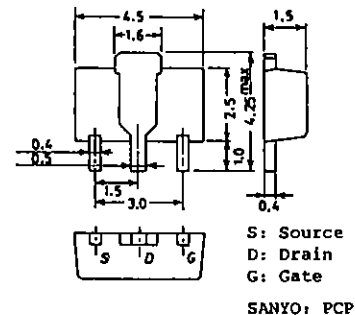
Marking: JE

Switching Time Test Circuit

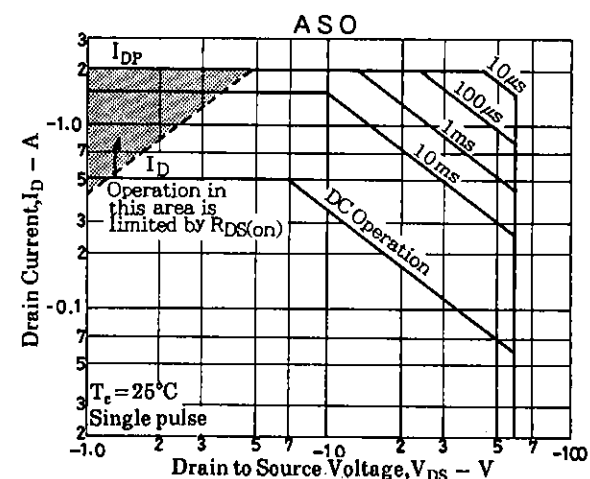
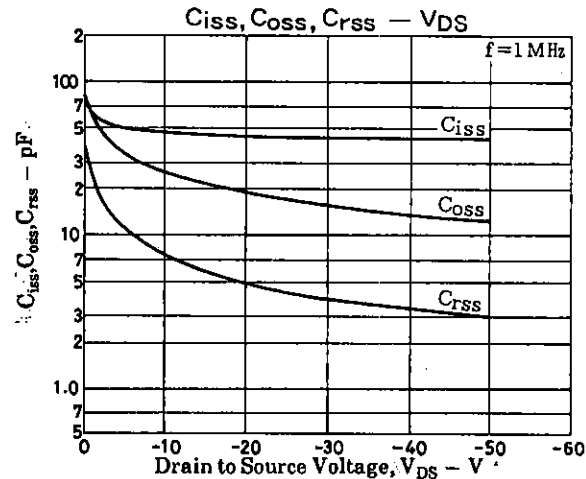
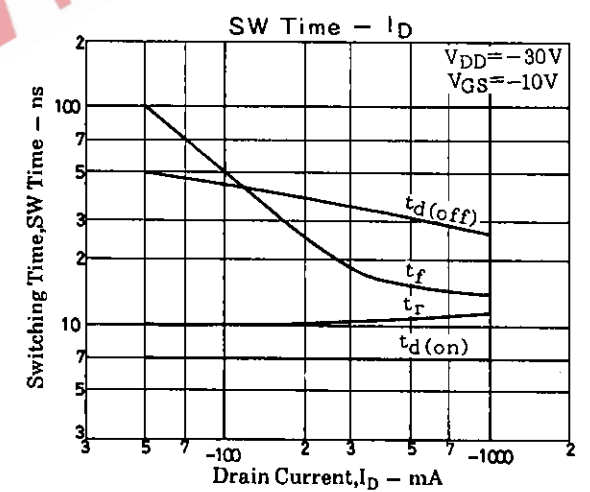
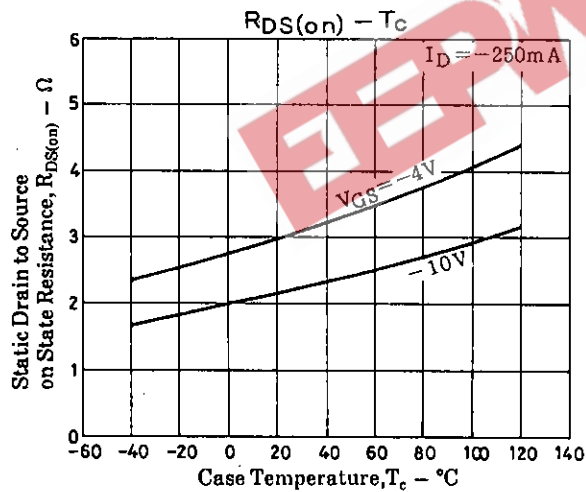
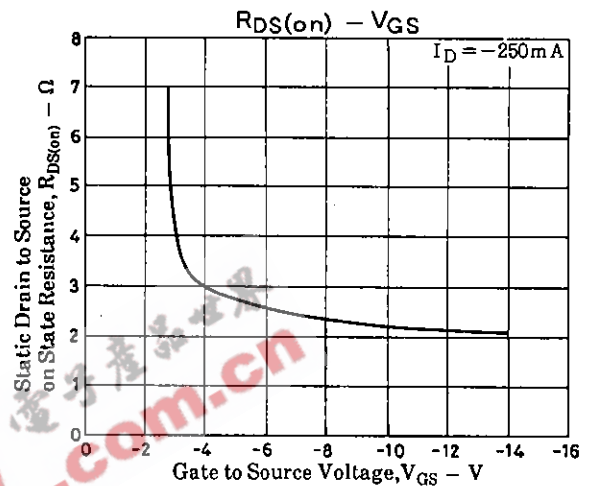
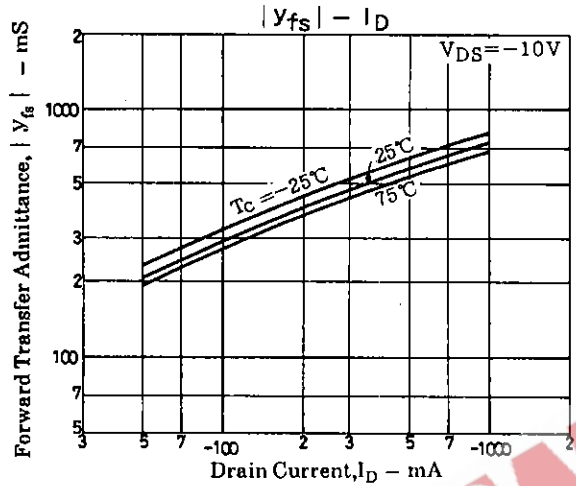
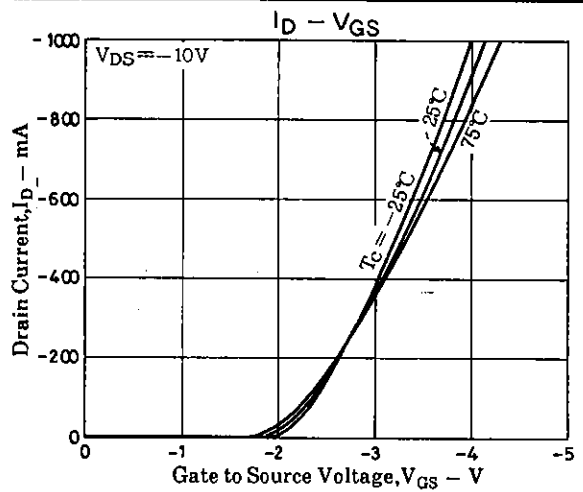
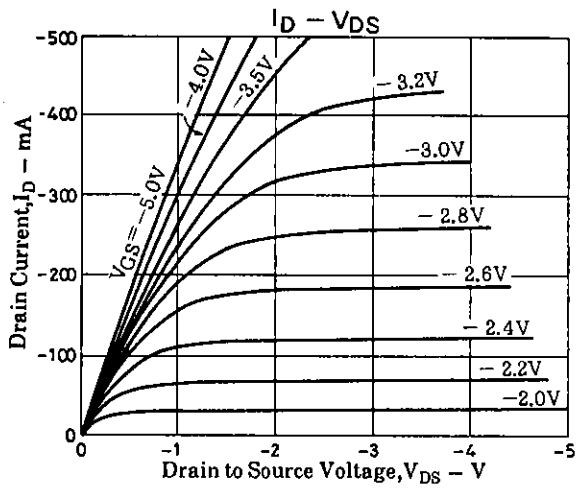


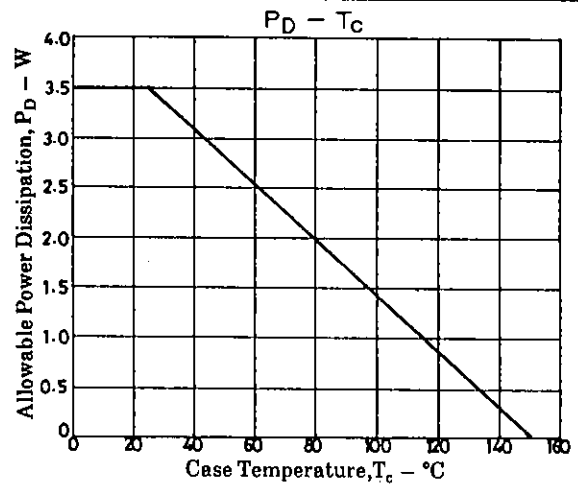
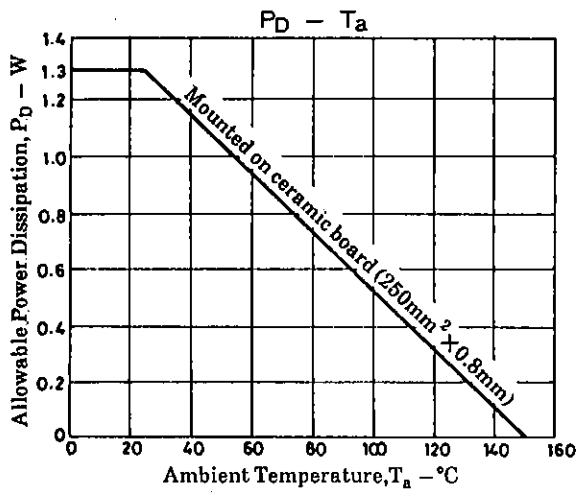
Package Dimensions 2062

(unit: mm)



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